

LONG CREEPAGE TYPE HIGH ISOLATION VOLTAGE  
4-PIN PHOTOCOUPLER

-NEPOC Series-

## DESCRIPTION

The PS2581L1, PS2581L2 are optically coupled isolators containing a GaAs light emitting diode and an NPN silicon phototransistor in a plastic DIP (Dual In-line Package).

Creepage distance and clearance of leads are over 8 millimeters.

The PS2581L2 is lead bending type (Gull-wing) for surface mounting.

## FEATURES

- Long creepage and clearance distance (8 mm)
- High isolation voltage (BV = 5 000 Vr.m.s.)
- High collector to emitter voltage ( $V_{CE0} = 80$  V)
- High-speed switching ( $t_r = 3 \mu\text{s}$  TYP.,  $t_f = 5 \mu\text{s}$  TYP.)
- High current transfer ratio (CTR = 200 % TYP.)
- UL approved: File No. E72422 (S)
- CSA approved: No. CA101391
- BSI approved: No. 8243/8244
- NEMKO approved: No. P97103006
- DEMKO approved: No. 307269
- SEMKO approved: No. 9741154/01
- FIMKO approved: No. 018277
- VDE0884 approved

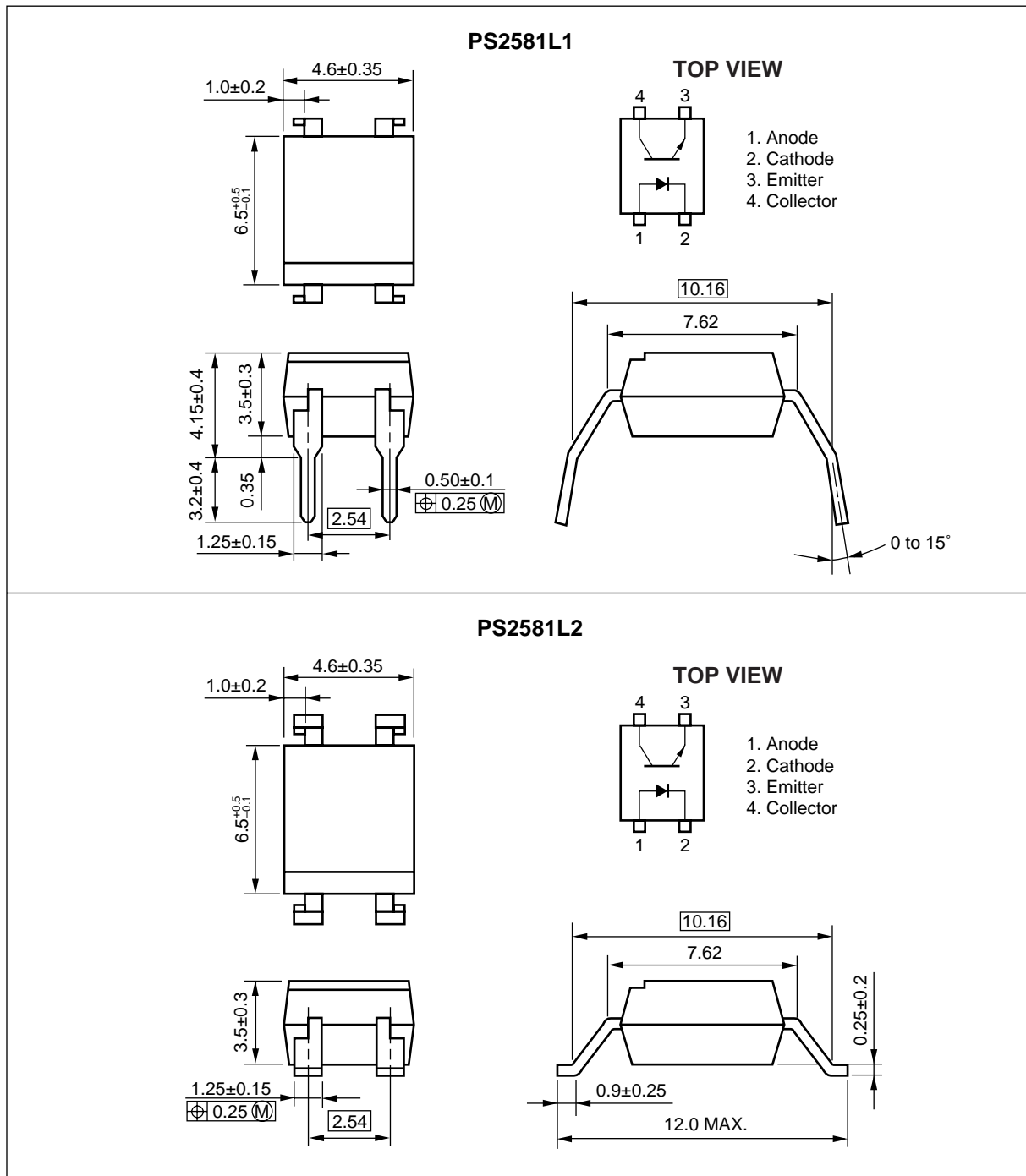
## ORDERING INFORMATION

Part Number	Package	Safety Standard Approval	Application Part Number <sup>*1</sup>
PS2581L1	4-pin DIP	UL, CSA, BSI, NEMKO, DEMKO,	PS2581L1
PS2581L2	4-pin DIP (lead bending surface mount)	SEMKO, FIMKO, VDE approved	PS2581L2
PS2581L2-E3, E4	4-pin DIP taping		

\*1 As applying to Safety Standard, following part number should be used.

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PACKAGE DIMENSIONS (in millimeters)



PHOTOCOUPLER CONSTRUCTION

Parameter	Unit (MIN.)
Air Distance	8 mm
Outer Creepage Distance	8 mm
Inner Creepage Distance	4 mm
Isolation Distance	0.4 mm

**ABSOLUTE MAXIMUM RATINGS (T<sub>A</sub> = 25 °C, unless otherwise specified)**

Parameter		Symbol	Ratings	Unit
Diode	Forward Current (DC)	I <sub>F</sub>	80	mA
	Reverse Voltage	V <sub>R</sub>	6	V
	Power Dissipation Derating	ΔP <sub>D</sub> /°C	1.5	mW/°C
	Power Dissipation	P <sub>D</sub>	150	mW
	Peak Forward Current *1	I <sub>FP</sub>	1	A
Transistor	Collector to Emitter Voltage	V <sub>CEO</sub>	80	V
	Emitter to Collector Voltage	V <sub>ECO</sub>	7	V
	Collector Current	I <sub>C</sub>	50	mA
	Power Dissipation Derating	ΔP <sub>C</sub> /°C	1.5	mW/°C
	Power Dissipation	P <sub>C</sub>	150	mW
Isolation Voltage *2		BV	5 000	Vr.m.s.
Operating Ambient Temperature		T <sub>A</sub>	-55 to +100	°C
Storage Temperature		T <sub>stg</sub>	-55 to +150	°C

\*1 PW = 100 μs, Duty Cycle = 1 %

\*2 AC voltage for 1 minute at T<sub>A</sub> = 25 °C, RH = 60 % between input and output

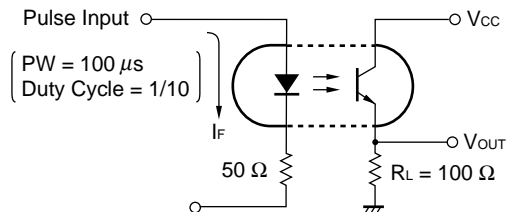
ELECTRICAL CHARACTERISTICS (T<sub>A</sub> = 25 °C)

Parameter		Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Diode	Forward Voltage	V <sub>F</sub>	I <sub>F</sub> = 10 mA		1.17	1.4	V
	Reverse Current	I <sub>R</sub>	V <sub>R</sub> = 5 V			5	μA
	Terminal Capacitance	C <sub>t</sub>	V = 0 V, f = 1.0 MHz		50		pF
Transistor	Collector to Emitter Dark Current	I <sub>CEO</sub>	V <sub>CE</sub> = 80 V, I <sub>F</sub> = 0 mA			100	nA
Coupled	Current Transfer Ratio (I <sub>c</sub> /I <sub>F</sub> ) <sup>*1</sup>	CTR	I <sub>F</sub> = 5 mA, V <sub>CE</sub> = 5 V	80	200	400	%
	Collector Saturation Voltage	V <sub>CE(sat)</sub>	I <sub>F</sub> = 10 mA, I <sub>c</sub> = 2 mA			0.3	V
	Isolation Resistance	R <sub>I-O</sub>	V <sub>I-O</sub> = 1.0 kV <sub>DC</sub>	10 <sup>11</sup>			Ω
	Isolation Capacitance	C <sub>I-O</sub>	V = 0 V, f = 1.0 MHz		0.5		pF
	Rise Time <sup>*2</sup>	t <sub>r</sub>	V <sub>CC</sub> = 10 V, I <sub>c</sub> = 2 mA, R <sub>L</sub> = 100 Ω		3		μs
	Fall Time <sup>*2</sup>	t <sub>f</sub>			5		

\*1 CTR rank

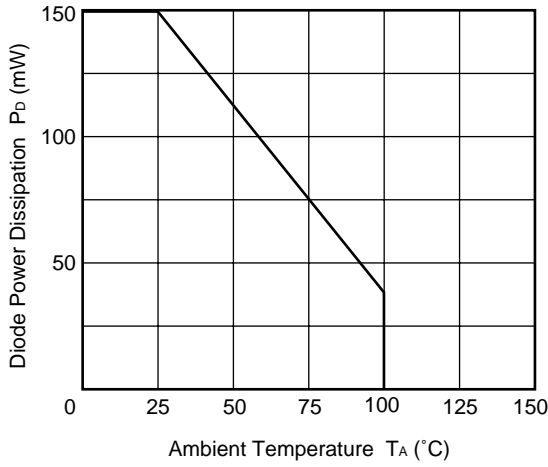
- L : 200 to 400 (%)
- M : 80 to 240 (%)
- D : 100 to 300 (%)
- H : 80 to 160 (%)
- W : 130 to 260 (%)
- N : 80 to 400 (%)

\*2 Test circuit for switching time

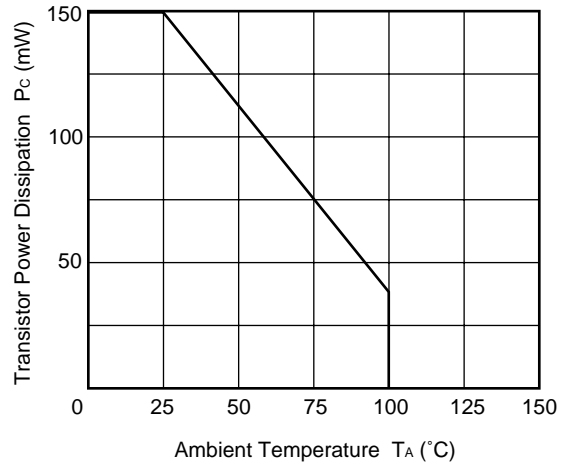


TYPICAL CHARACTERISTICS ( $T_A = 25\text{ }^\circ\text{C}$ , unless otherwise specified)

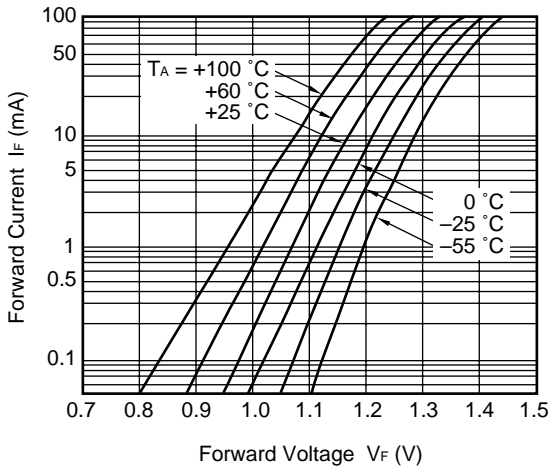
DIODE POWER DISSIPATION vs. AMBIENT TEMPERATURE



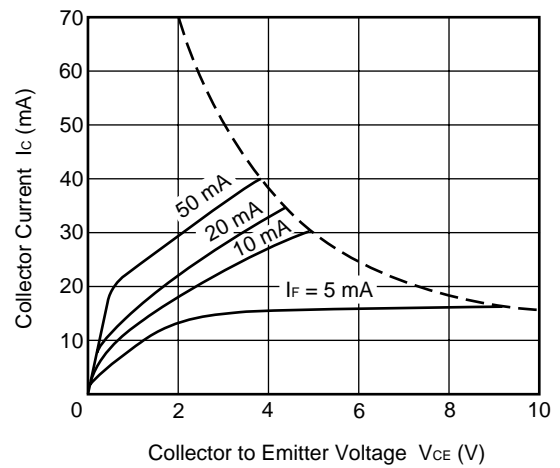
TRANSISTOR POWER DISSIPATION vs. AMBIENT TEMPERATURE



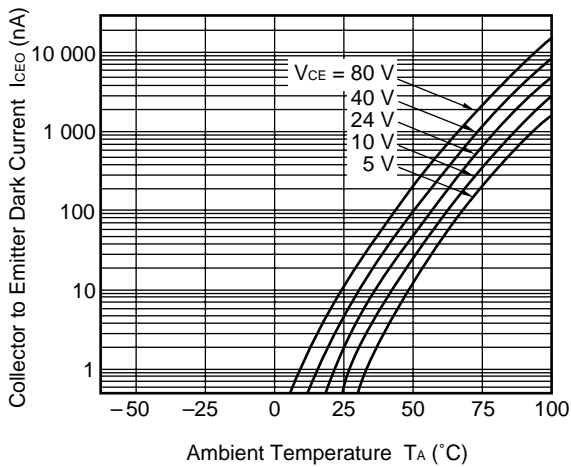
FORWARD CURRENT vs. FORWARD VOLTAGE



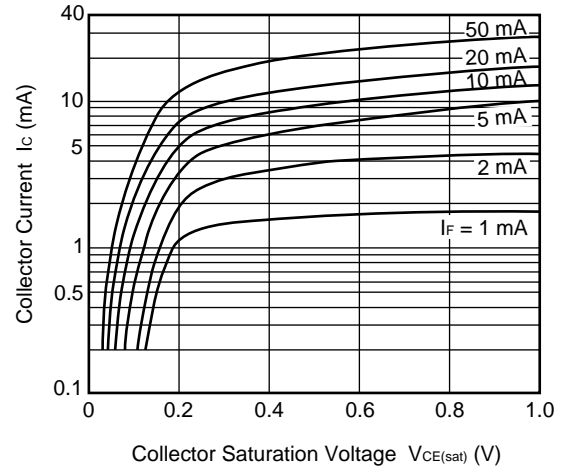
COLLECTOR CURRENT vs. COLLECTOR TO EMITTER VOLTAGE



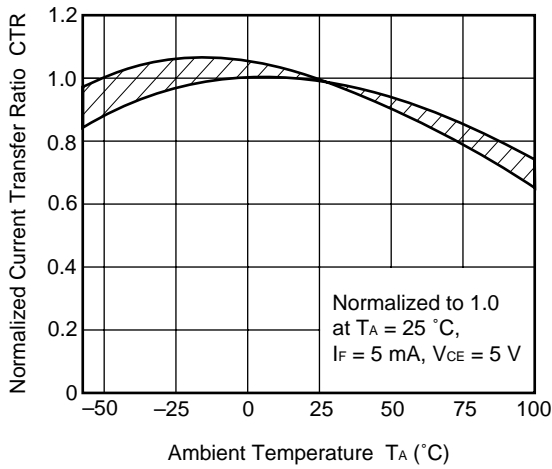
COLLECTOR TO EMITTER DARK CURRENT vs. AMBIENT TEMPERATURE



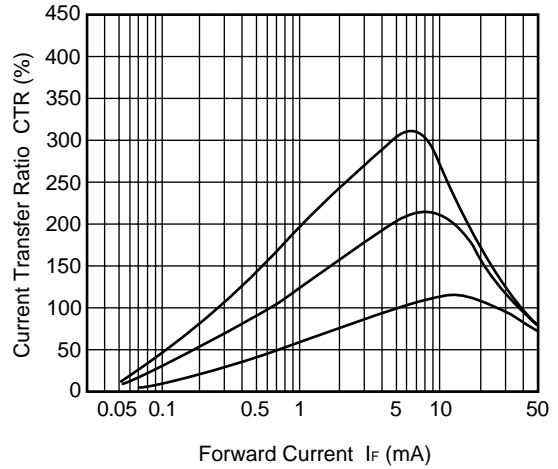
COLLECTOR CURRENT vs. COLLECTOR SATURATION VOLTAGE



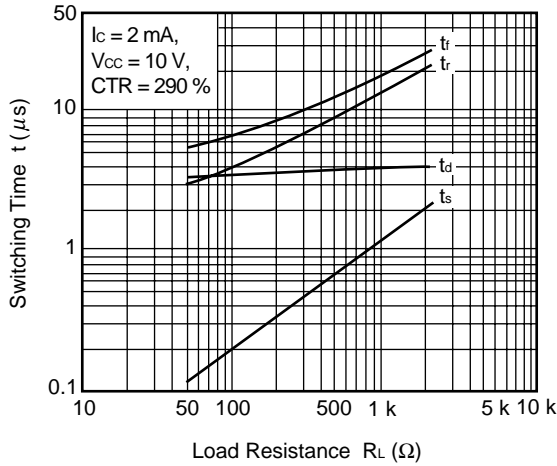
NORMALIZED CURRENT TRANSFER RATIO vs. AMBIENT TEMPERATURE



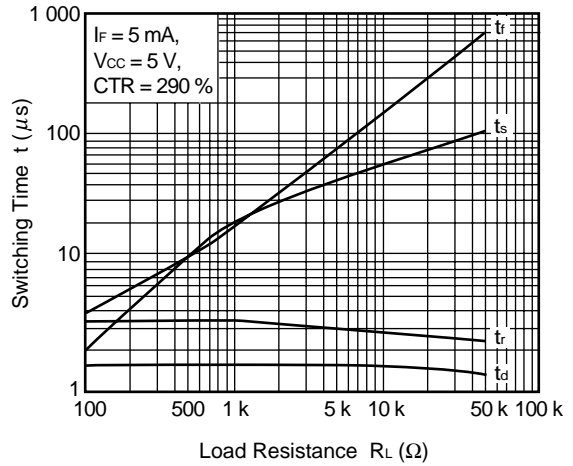
CURRENT TRANSFER RATIO vs. FORWARD CURRENT



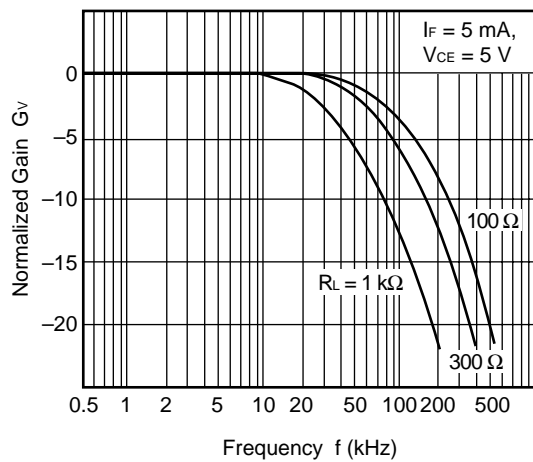
SWITCHING TIME vs. LOAD RESISTANCE



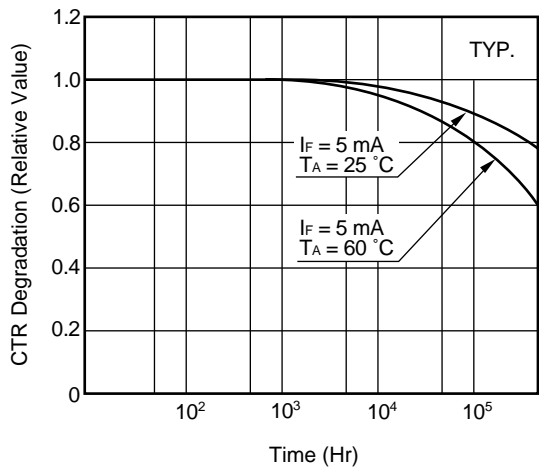
SWITCHING TIME vs. LOAD RESISTANCE



FREQUENCY RESPONSE



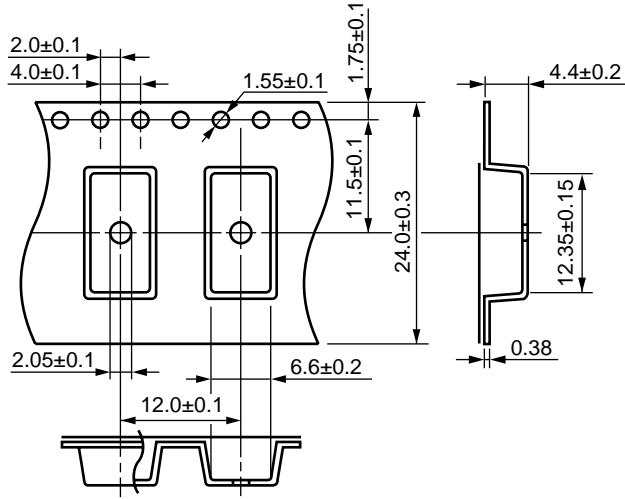
LONG TERM CTR DEGRADATION



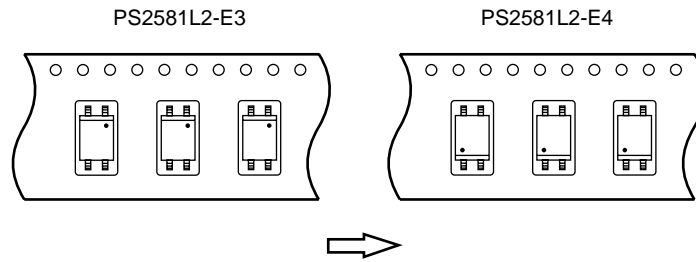
Remark The graphs indicate nominal characteristics.

★ TAPING SPECIFICATIONS (in millimeters)

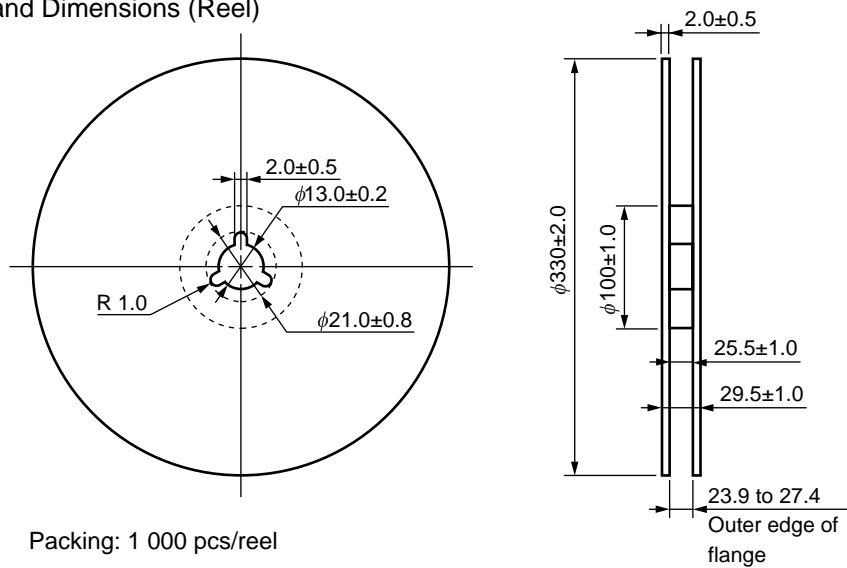
Outline and Dimensions (Tape)



Tape Direction



Outline and Dimensions (Reel)



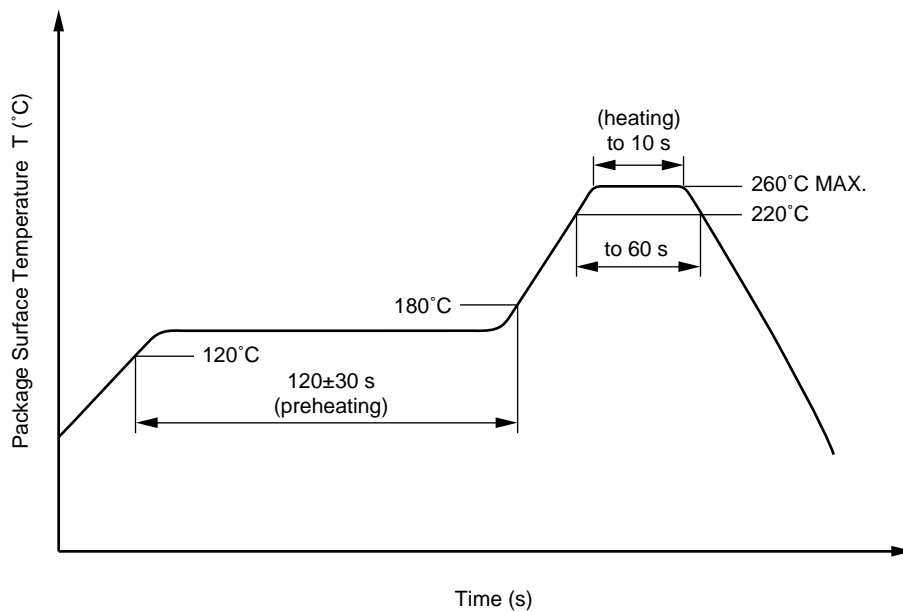
★ NOTES ON HANDLING

1. Recommended soldering conditions

(1) Infrared reflow soldering

- Peak reflow temperature 260°C or below (package surface temperature)
- Time of peak reflow temperature 10 seconds or less
- Time of temperature higher than 220°C 60 seconds or less
- Time to preheat temperature from 120 to 180°C 120±30 s
- Number of reflows Three
- Flux Rosin flux containing small amount of chlorine (The flux with a maximum chlorine content of 0.2 Wt% is recommended.)

Recommended Temperature Profile of Infrared Reflow



(2) Wave soldering

- Temperature 260°C or below (molten solder temperature)
- Time 10 seconds or less
- Preheating conditions 120°C or below (package surface temperature)
- Number of times One (Allowed to be dipped in solder including plastic mold portion.)
- Flux Rosin flux containing small amount of chlorine (The flux with a maximum chlorine content of 0.2 Wt% is recommended.)

(3) Cautions

- Fluxes  
Avoid removing the residual flux with freon-based and chlorine-based cleaning solvent.

2. Cautions regarding noise

Be aware that when voltage is applied suddenly between the photocoupler's input and output or between collector-emitters at startup, the output side may enter the on state, even if the voltage is within the absolute maximum ratings.



**★ USAGE CAUTIONS**

1. Protect against static electricity when handling.
2. Avoid storage at a high temperature and high humidity.

SPECIFICATION OF VDE MARKS LICENSE DOCUMENT (VDE0884)

Parameter	Symbol	Speck	Unit
Application classification (DIN VDE 0109) for rated line voltages $\leq 300$ Vr.m.s. for rated line voltages $\leq 600$ Vr.m.s.		IV III	
Climatic test class (DIN IEC 68 Teil 1/09.80)		55/100/21	
Dielectric strength maximum operating isolation voltage. Test voltage (partial discharge test procedure a for type test and random test) $U_{pr} = 1.2 \times U_{IORM}$ , $P_d < 5$ pC	$U_{IORM}$ $U_{pr}$	890 1 068	$V_{peak}$ $V_{peak}$
★ Test voltage (partial discharge test procedure b for all devices test) $U_{pr} = 1.6 \times U_{IORM}$ , $P_d < 5$ pC	$U_{pr}$	1 424	$V_{peak}$
Highest permissible overvoltage	$U_{TR}$	8 000	$V_{peak}$
Degree of pollution (DIN VDE 0109)		2	
Clearance distance		> 8.0	mm
Creepage distance		> 8.0	mm
Comparative tracking index (DIN IEC 112/VDE 0303 part 1)	CTI	175	
Material group (DIN VDE 0109)		III a	
Storage temperature range	$T_{stg}$	-55 to +150	°C
Operating temperature range	$T_A$	-55 to +100	°C
Isolation resistance, minimum value $V_{IO} = 500$ V dc at $T_A = 25$ °C $V_{IO} = 500$ V dc at $T_A$ MAX. at least 100 °C	Ris MIN. Ris MIN.	$10^{12}$ $10^{11}$	$\Omega$ $\Omega$
Safety maximum ratings (maximum permissible in case of fault, see thermal derating curve) Package temperature Current (input current $I_F$ , $\Psi_i = 0$ ) Power (output or total power dissipation) Isolation resistance $V_{IO} = 500$ V dc at $T_A = 175$ °C ( $T_{si}$ )	$T_{si}$ $I_{si}$ $\Psi_{si}$ Ris MIN.	175 400 700 $10^9$	°C mA mW $\Omega$

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M8E 00.4-0110

**SAFETY INFORMATION ON THIS PRODUCT**

<p><b>Caution</b></p>	<p>GaAs Products</p>	<p>The product contains gallium arsenide, GaAs. GaAs vapor and powder are hazardous to human health if inhaled or ingested.</p> <ul style="list-style-type: none"> <li>• Do not destroy or burn the product.</li> <li>• Do not cut or cleave off any part of the product.</li> <li>• Do not crush or chemically dissolve the product.</li> <li>• Do not put the product in the mouth.</li> </ul> <p>Follow related laws and ordinances for disposal. The product should be excluded from general industrial waste or household garbage.</p>
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